

**DMG204B1**

Silicon NPN epitaxial planar type (Tr1)  
Silicon PNP epitaxial planar type (Tr2)

For low frequency amplification

## ■ Features

- High forward current transfer ratio  $h_{FE}$  with excellent linearity
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Halogen-free / RoHS compliant  
(EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: C5

## ■ Basic Part Number

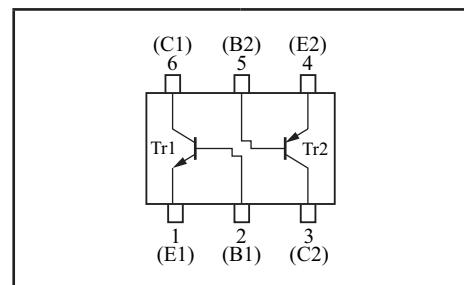
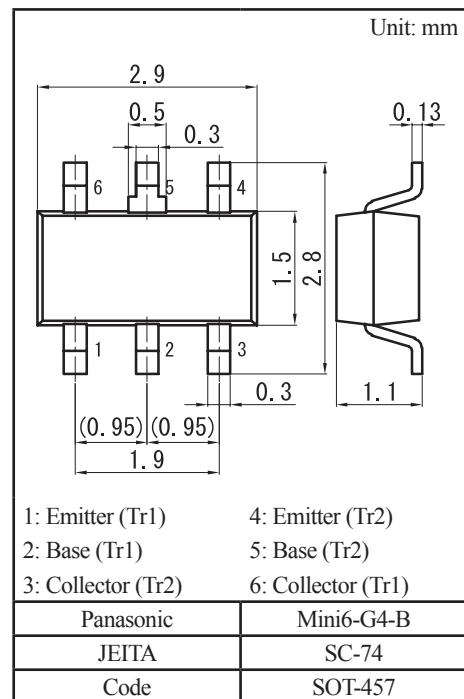
DSC2501 + DSA2001 (Individual)

## ■ Packaging

DMG204B10R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

### ■ Absolute Maximum Ratings $T_s = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	25	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	20	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	12	V
	Collector current	$I_C$	0.5	A
	Peak collector current	$I_{CP}$	1	A
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	-60	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	-50	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	-7	V
	Collector current	$I_C$	-100	mA
	Peak collector current	$I_{CP}$	-200	mA
Overall	Total power dissipation	$P_T$	300	mW
	Junction temperature	$T_j$	150	°C
	Operating ambient temperature	$T_{opr}$	-40 to +85	°C
	Storage temperature	$T_{stg}$	-55 to +150	°C



■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$ 

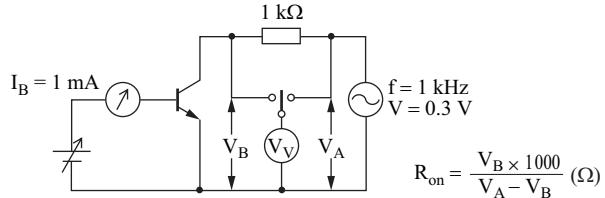
## • Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	25			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	20			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	12			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 25 \text{ V}, I_E = 0$			100	nA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 2 \text{ V}, I_C = 0.5 \text{ A}$	200		800	—
Collector-emitter saturation voltage <sup>*1</sup>	$V_{CE(\text{sat})}$	$I_C = 0.5 \text{ A}, I_B = 20 \text{ mA}$		0.18	0.40	V
Base-emitter saturation voltage <sup>*1</sup>	$V_{BE(\text{sat})}$	$I_C = 0.5 \text{ A}, I_B = 50 \text{ mA}$			1.2	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_C = 50 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		6		pF
ON resistance <sup>*2</sup>	$R_{on}$			1.0		$\Omega$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. <sup>\*1</sup>: Pulse measurement

<sup>\*2</sup>: Ron measurement circuit

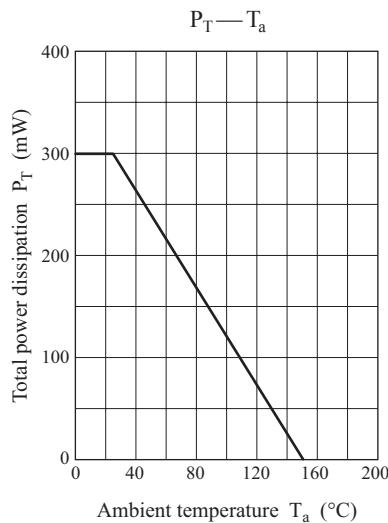


## • Tr2

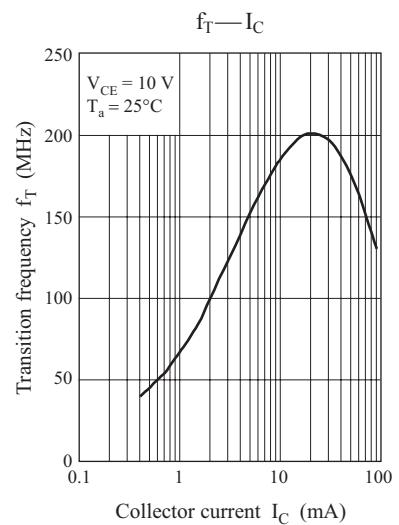
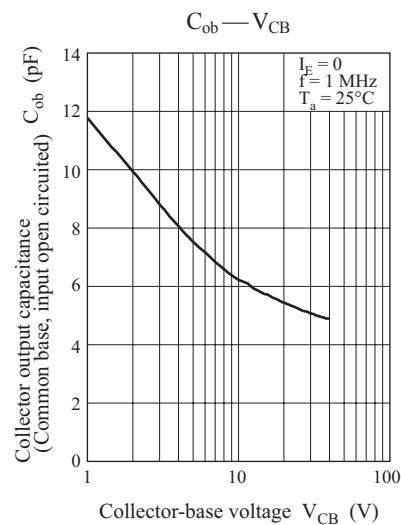
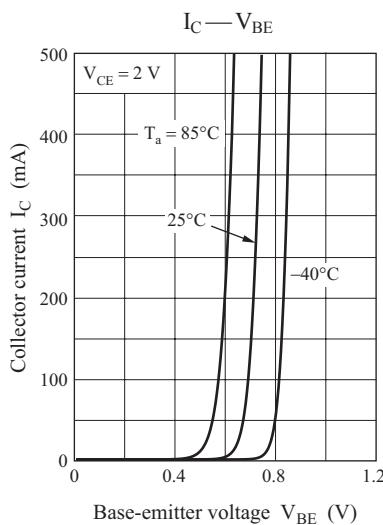
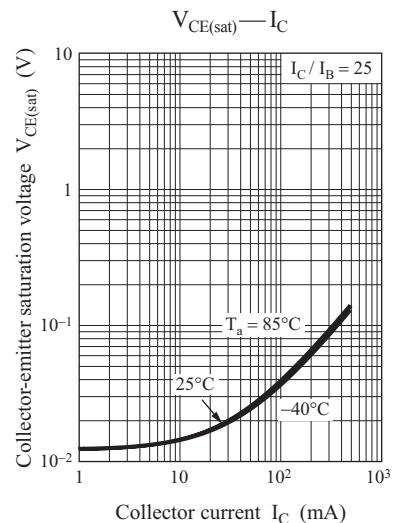
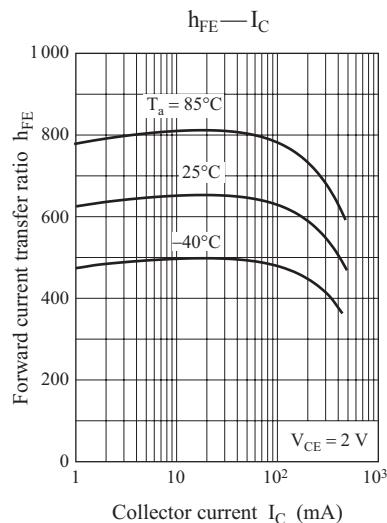
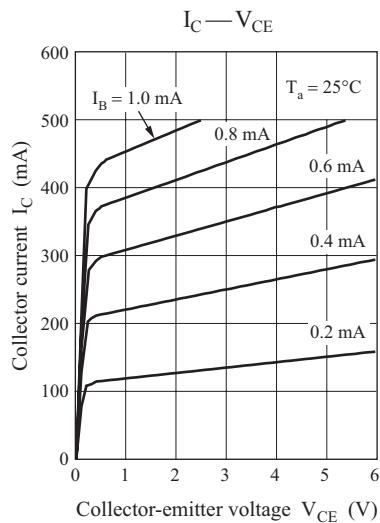
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -10 \mu\text{A}, I_E = 0$	-60			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -20 \text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -10 \text{ V}, I_B = 0$			-100	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}, I_C = -2 \text{ mA}$	210		460	—
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		-0.2	-0.5	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}, I_C = -2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2		pF

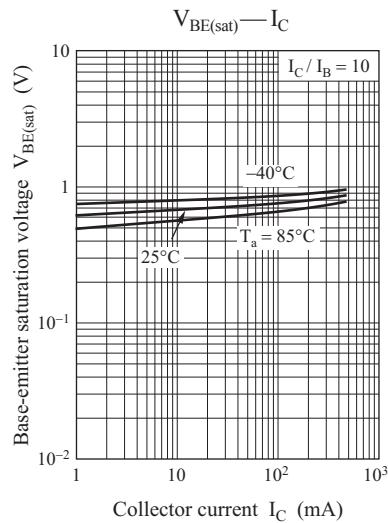
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

## Common characteristics chart

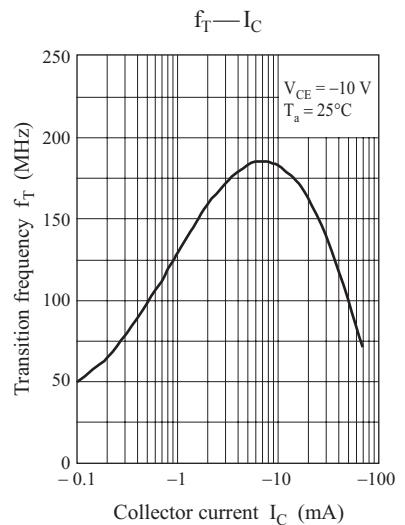
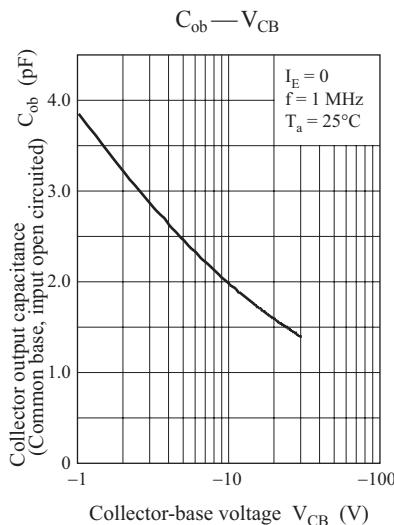
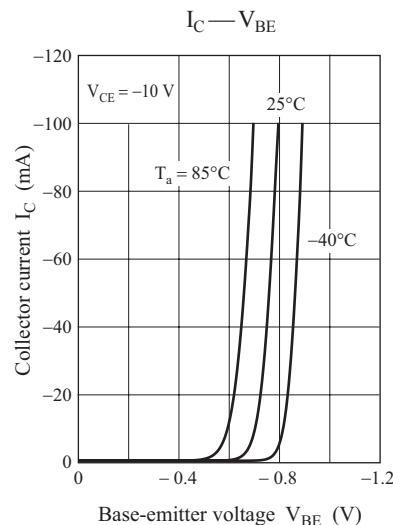
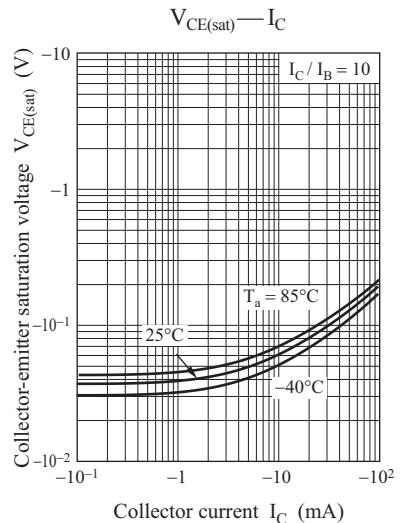
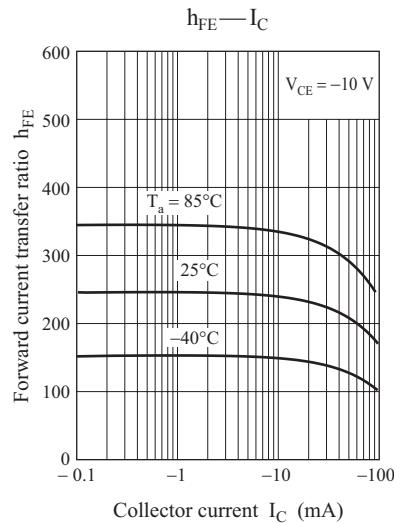
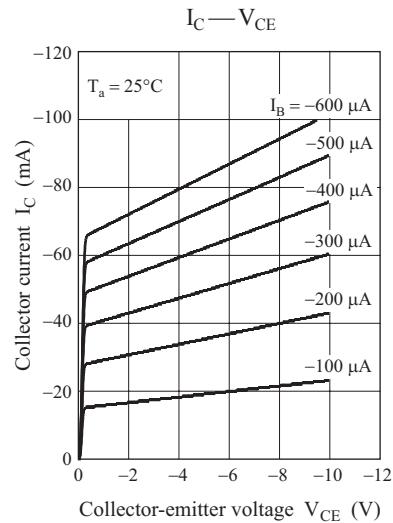


## Characteristics charts of Tr1



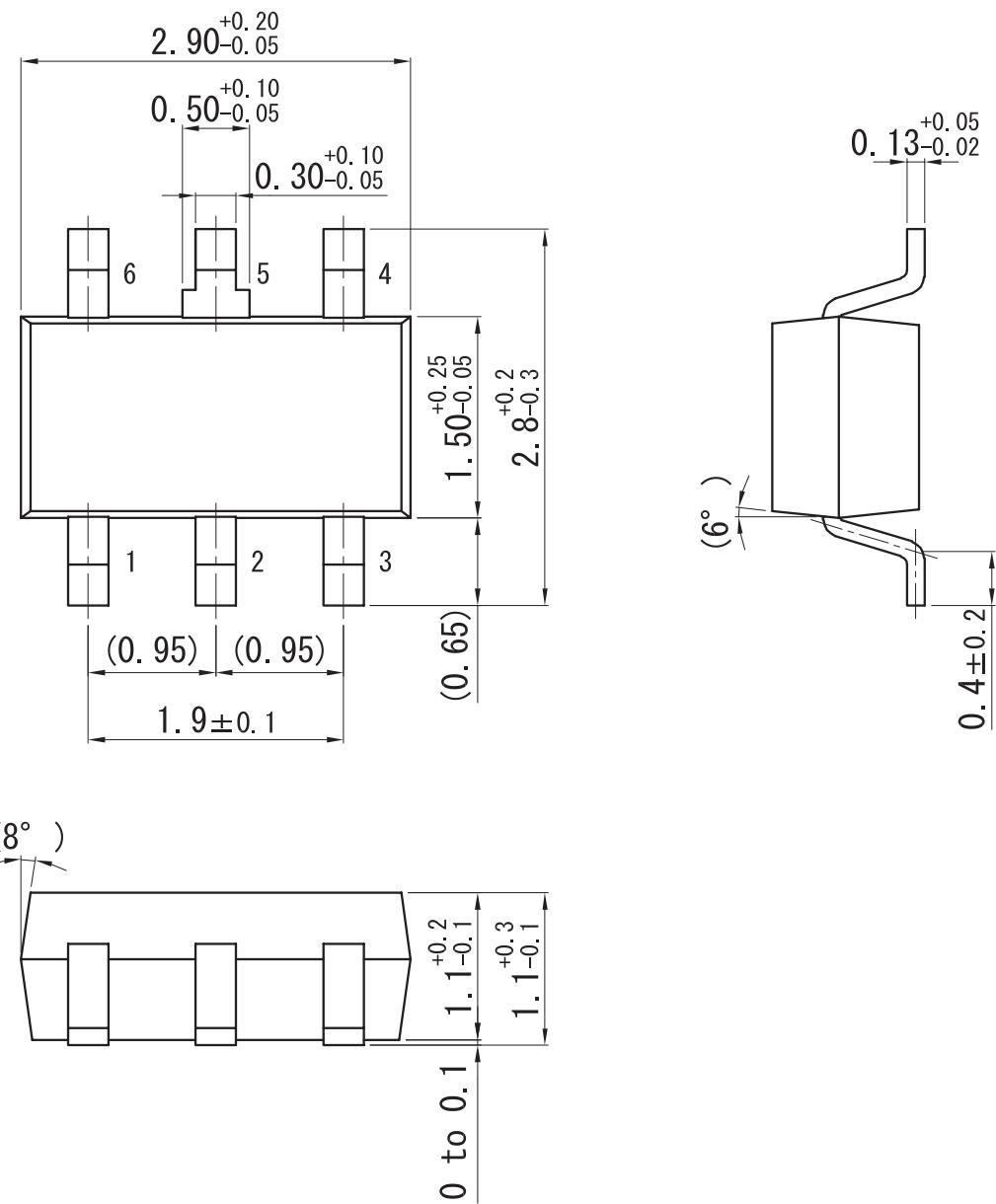


**Characteristics charts of Tr2**

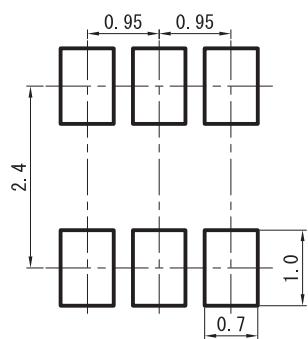


## Mini6-G4-B

Unit: mm



## ■ Land Pattern (Reference) (Unit: mm)



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